

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re the Application of

Jun-ichiro FURIHATA, Kiyoshi MITANI

Application No.: U. S. National Stage of  
PCT/JP00/04634

Filed: March 13, 2001

Docket No.: 108868

For: A METHOD OF PRODUCING A BONDED WAFER AND THE BONDED WAFER

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-16 without prejudice to or disclaimer of the subject matter contained therein.

Please add new claims 17-34 as follows:

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17. A method of producing a bonded wafer comprising bonding a bond wafer made of silicon single crystal and a base wafer via an oxide film or directly and then reducing thickness of the bond wafer, wherein the base wafer is a wafer produced by processes comprising slicing a silicon single crystal ingot, and then subjected at least to chamfering, lapping, etching, mirror polishing and cleaning, and the etching process is conducted by subjecting the wafer to alkali etching, and then acid etching, and an etching amount in the alkali etching is larger than an etching amount in the acid etching.